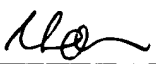


ITW

CERTIFICATE OF MAILING UNDER 37 CFR 1.8(a)
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail
in an envelope addressed to: Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450.


H. C. Chan

4/16/05
Date

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hyun-Jin Cho, et al.)	Examiner: Tran, Mai Huong C
)	
Serial No.: 10/666,220)	Group Art Unit: 2818
)	
Filed: September 19, 2003)	
)	
For: Stability in Thyristor-Based Memory Device)	
)	

SUBMISSION OF DOCUMENTS REQUESTED BY EXAMINER

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450


Sir:

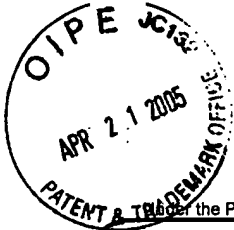
In the Office Action dated March 28, 2005, the Examiner requested the submission of copies of three documents. Enclosed are the requested documents. Also enclosed is a copy of a previous submitted PTO-1449 listing these references. Please initial the PTO-1449 after considering the references.

The Commissioner is authorized to charge any fees in this submission to deposit account 50-2538 (docket number C002-D-2)

Date: April 16, 2005

Respectfully submitted,


Hark C. Chan (Reg. No. 35,477)



PTO/SB/08B (08-03)

Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	10/666,220
Filing Date	9/19/2003
First Named Inventor	Cho
Art Unit	2818
Examiner Name	Tran, Mai Huong C
Attorney Docket Number	C002-D-2

Sheet 2 of 2

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Nemati, Farid and Plummer, James, D., A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device, VLSI Technology Technical Digest, 6/1998	
		Nemati, Farid and Plummer, James, D., A Novel Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-scale Memories, International Electron Device Meeting Technical Digest, 1999	
		Gribnikov, Z.S., Korobov, V.A., and Mitin, V.V., The Tunnel Diodoe as a Thyristor Emitter, Solid-State Electronics, Vol. 42, No. 9, 1998, pp. 1761-1763	

Examiner
SignatureDate
Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.